

PMBTA42

300 V, 100 mA NPN high-voltage transistor Rev. 05 — 12 December 2008

Product data sheet

Product profile

1.1 General description

NPN high-voltage transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBTA92.

1.2 Features

■ High voltage (max. 300 V)

1.3 Applications

Telephony and professional communication equipment

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------|-------------------------|-----|-----|-----|------|
| V_{CEO} | collector-emitter voltage | open base | - | - | 300 | V |
| I _C | collector current | | - | - | 100 | mA |
| h _{FE} | DC current gain | $V_{CE} = 10 \text{ V}$ | | | | |
| | | $I_C = 1 \text{ mA}$ | 25 | - | - | |
| | | $I_C = 10 \text{ mA}$ | 40 | - | - | |
| | | $I_C = 30 \text{ mA}$ | 40 | - | - | |

Pinning information 2.

Table 2. **Pinning**

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------|--|----------------|
| 1 | base | | |
| 2 | emitter | <u> </u> | 3 |
| 3 | collector | 1 2 | 1 — 2 |
| | | | sym021 |



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3. Ordering information

Table 3. Ordering information

| Type number[1] | Package | | | | | |
|----------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMBTA42 | - | plastic surface-mounted package; 3 leads | SOT23 | | | |
| PMBTA42/DG | _ | | | | | |

^{[1] /}DG: halogen-free

4. Marking

Table 4. Marking codes

| Type number[1] | Marking code ^[2] |
|----------------|-----------------------------|
| PMBTA42 | *1D |
| PMBTA42/DG | *BV |

^{[1] /}DG: halogen-free

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|---|--------------|------|------|
| V_{CBO} | collector-base voltage | open emitter | - | 300 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 300 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 6 | V |
| Ic | collector current | | - | 100 | mA |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | 200 | mA |
| I _{BM} | peak base current | single pulse; $t_p \le 1 \text{ ms}$ | - | 100 | mA |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | <u>[1]</u> - | 250 | mW |
| T _j | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T_{stg} | storage temperature | | -65 | +150 | °C |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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^{[2] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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Thermal characteristics

Table 6. **Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------|---|-------------|-------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] - | - | 500 | K/W |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Characteristics 7.

Product data sheet

Characteristics Table 7.

 $T_{amb} = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|--|-----|-----|-----|------|
| I _{CBO} | collector-base cut-off current | $V_{CB} = 200 \text{ V}; I_E = 0 \text{ A}$ | - | - | 100 | nA |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}$ | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 10 V | | | | |
| | | I _C = 1 mA | 25 | - | - | |
| | | $I_C = 10 \text{ mA}$ | 40 | - | - | |
| | | $I_C = 30 \text{ mA}$ | 40 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$ | - | - | 500 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$ | - | - | 900 | mV |
| C _{re} | feedback capacitance | $V_{CB} = 20 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz | - | - | 3 | pF |
| f _T | transition frequency | $V_{CE} = 20 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz | 50 | - | - | MHz |

8. Package outline

Plastic surface-mounted package; 3 leads

SOT23

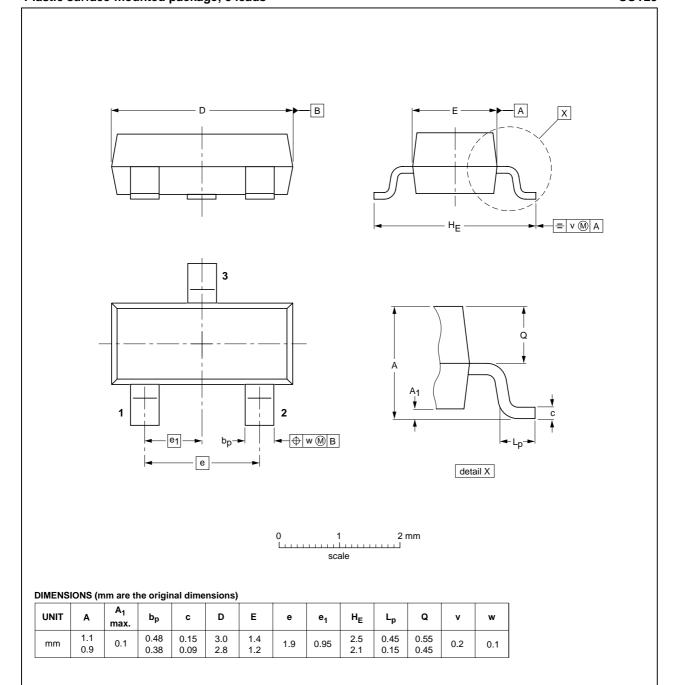


Fig 1. Package outline SOT23 (TO-236AB)

IEC

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JEITA

REFERENCES

JEDEC

TO-236AB

OUTLINE

VERSION

SOT23

ISSUE DATE

04-11-04

06-03-16

EUROPEAN

PROJECTION

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9. Packing information

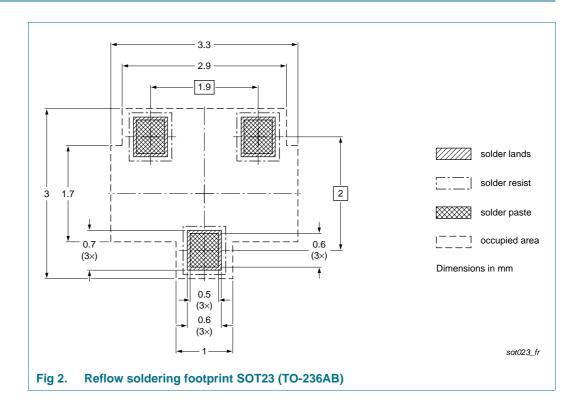
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

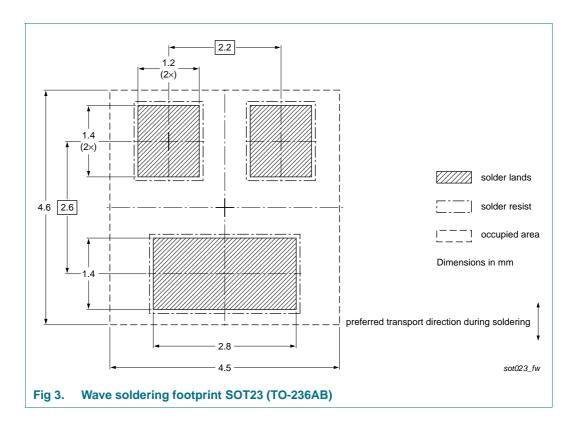
| Type number | Package | Description | Packing quantity | |
|-------------|---------|--------------------------------|------------------|-------|
| | | | 3000 | 10000 |
| PMBTA42 | SOT23 | 4 mm pitch, 8 mm tape and reel | -215 | -235 |
| PMBTA42/DG | | | | |

- [1] For further information and the availability of packing methods, see Section 13.
- [2] /DG: halogen-free

10. Soldering



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11. Revision history

Table 9. Revision history

| | • | | | |
|----------------|---------------------------------|--|------------------------|-----------------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| PMBTA42_5 | 20081212 | Product data sheet | - | PMBTA42_4 |
| Modifications: | | t of this data sheet has been of NXP Semiconductors. | redesigned to comply v | vith the new identity |
| | Legal texts | s have been adapted to the r | new company name whe | ere appropriate. |
| | Type numb | oer PMBTA42/DG added | | |
| | Table 4 "M | arking codes": enhanced | | |
| | Section 12 | "Legal information": updated | d | |
| PMBTA42_4 | 20040122 | Product specification | - | PMBTA42_3 |
| PMBTA42_3 | 19990422 | Product specification | - | PMBTA42_43_CNV_2 |
| | | | | |

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12. Legal information

12.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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